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## IN THE UNITED STATES PATEN ADEMARK OFFICE

In re patent application of

Tatsuya Usami

Serial No.:

09/851,313

**Group Art Unit:** 

2823

Filing Date: May 9, 2001

Examiner:

Maldonado, Julio J.

SEMICONDUCTOR DEVICE AND SEMICONDUCTOR WAFER HAVING

MULTI-LAYERED INSULATION FILM

Commissioner for Patents Alexandria, VA 22313-1450

## INFORMATION DISCLOSURE STATEMENT

Sir:

Under the provisions of 37 CFR §1.97 through §1.99 and pursuant to applicant's duty of disclosure under 37 CFR §1.56, applicant respectfully brings the following documents listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. All of these references were cited by the Examiner in the co-pending Application No. 10/135,393, in an Office Action dated January 4, 2005.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which the applicant is aware.

I hereby certify that no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in § 1.56(c) more than three months prior to the filing of the information disclosure statement.

It is respectfully requested that the listed reference be considered by the Examiner and formally made of record in this application.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

espectfully submitted,

Registration No. 46,060

Date:

McGinn'& Gibb, PLLC

Intellectual Property Law

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OF					Docket Number (Optional) NEC01P069-MSb		Application Number		
INFORMATION DISCLOSURE OF ATION (Use several sheets if necessary)					Applicant(s)	09/851,313			
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-		75.41.7 to 1	FEVT & TRADE	S. PAT	ENT DOCUMENTS				
*EXAMINER INTITAL	REF	DOCUMENT NUMBER	DATE	NAME		CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
·		6,624,061 B2	09/23/03	Aoki					
		6,800,928 B1	10/05/04	Lee et al.					
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FOREIGN PATENT DOCUMENTS									
	REF	DOCUMENT NUMBER	DATE		COUNTRY	CLASS	SUBCLASS	Translation YES NO	
		*					Date, Pertinent Pa		
Sun-Young Kim et al., HOSP as a Low Dielectric Material: Comparative Study Against Hydrogen Silesesquioxane IEEE, 28-221								, 1999	
EXAMINER					DATE CONSIDERED				
		al if citation considered, whether clude copy of this form with next			ce with MPEP Section 609; D	raw line thro	ugh citation if not	in conform	ance and
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Form PTO-A820 (also form PTO-1449)